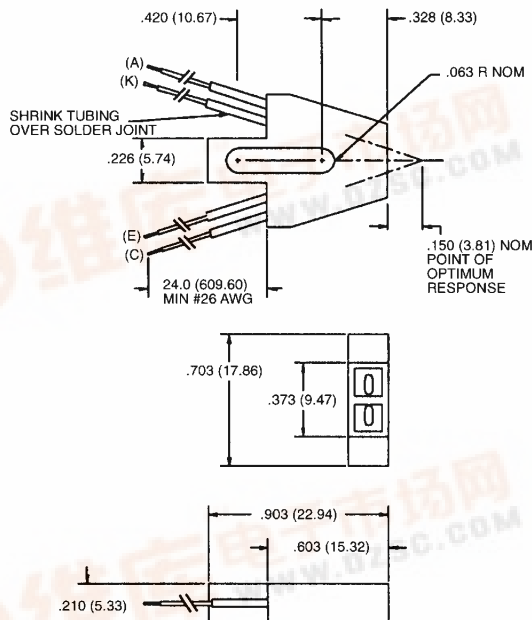




## REFLECTIVE OBJECT SENSOR

### QRC1133

#### PACKAGE DIMENSIONS



ST1781

FUNCTION	WIRE COLOR
(C) COLLECTOR	WHITE
(E) EMITTER	BLUE
(K) CATHODE	GREEN
(A) ANODE	ORANGE

#### NOTES:

- DIMENSIONS ARE IN INCHES (mm).
- TOLERANCE IS  $\pm .010$  (.25) UNLESS OTHERWISE SPECIFIED.

#### DESCRIPTION

The QRC1133 consists of an infrared emitting diode and an NPN silicon phototransistor mounted side by side on a converging optical axis in a black plastic housing. The phototransistor responds to radiation from the emitting diode only when a reflective object passes within its field of view. The area of optimum response approximates a circle .200" in diameter.

#### FEATURES

- Phototransistor output
- High Sensitivity
- Low cost plastic housing
- #26 AWG, 24 inch PVC wire termination



## REFLECTIVE OBJECT SENSOR

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Storage Temperature	$-40^\circ\text{C}$ to $+85^\circ\text{C}$
Operating Temperature	$-40^\circ\text{C}$ to $+85^\circ\text{C}$
Soldering:	
Lead Temperature (Iron)	$240^\circ\text{C}$ for 5 sec. <sup>(2,3,4)</sup>
Lead Temperature (Flow)	$260^\circ\text{C}$ for 10 sec. <sup>(2,3)</sup>

#### INPUT DIODE

Continuous Forward Current	50 mA
Reverse Voltage	5.0 Volts
Power Dissipation	100 mW <sup>(1)</sup>

#### OUTPUT TRANSISTOR

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Collector Current	40 mA
Power Dissipation	100 mW <sup>(1)</sup>

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
<b>INPUT DIODE</b>						
Forward Voltage	$V_F$	—		1.70	V	$I_F = 40\text{ mA}$
Reverse Leakage Current	$I_R$	—		100	$\mu\text{A}$	$V_R = 2.0\text{ V}$
<b>OUTPUT TRANSISTOR</b>						
Emitter-Collector Breakdown	$BV_{CEO}$	5		—	V	$I_E = 100\text{ }\mu\text{A}$
Collector-Emitter Breakdown	$BV_{CEO}$	30		—	V	$I_C = 1.0\text{ mA}$
Collector-Emitter Leakage	$I_{CEO}$	—		100	nA	$V_{CE} = 10.0\text{ V}$
<b>COUPLED</b>						
On-State Collector Current	$I_{C(ON)}$	0.20		—	mA	$I_F = 40\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $D = .150''$ <sup>(5,7)</sup>
Crosstalk	$I_{CX}$	—		1.00	$\mu\text{A}$	$I_F = 40\text{ mA}$ , $V_{CE} = 5\text{ V}$ <sup>(6)</sup>
Saturation Voltage	$V_{CE(SAT)}$	—		0.40	V	$I_F = 40\text{ mA}$ , $I_C = 0.1\text{ mA}$ , $D = .150''$

### NOTES

- Derate power dissipation linearly 1.67 mW/ $^\circ\text{C}$  above  $25^\circ\text{C}$ .
- RMA flux is recommended.
- Methanol or Isopropyl alcohols are recommended as cleaning agents.
- Soldering iron tip  $\frac{1}{16}''$  (1.6 mm) from housing.
- D is the distance from the assembly face to the reflective surface.
- Cross talk is the photocurrent measured with current to the input diode and no reflecting surface.
- Measured using Eastman Kodak neutral test card with 90% diffused reflecting surface.